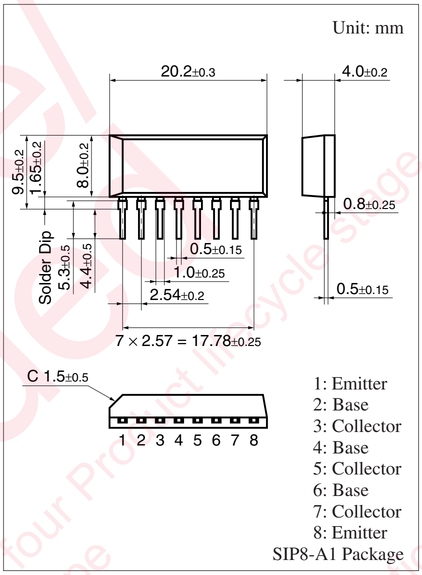
PUA3210 (PU3210)

Silicon PNP epitaxial planar type

For power amplification
Complementary to PUA3110 (PU3110)



Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Satisfactory linearity of forward current transfer ratio h_{FE}
- Large collector current I_C
- PNP 3 elements

Absolute Maximum Ratings $T_C = 25°C$

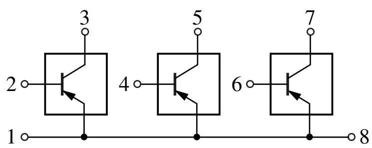
Parameter		Symbol	Rating	Unit
Collector-base voltage (Emitter open)		V_{CBO}	–60	V
Collector-emitter voltage (Base open)		V_{CEO}	–60	V
Emitter-base voltage (Collector open)		V_{EBO}	–6	V
Collector current		I_C	–3	A
Peak collector current		I_{CP}	–5	A
Base current		I_B	–1	A
Collector power dissipation		P_C	15	W
	$T_a = 25°C$		2.4	
Junction temperature		T_j	150	°C
Storage temperature		T_{stg}	–55 to +150	°C

Electrical Characteristics $T_C = 25°C \pm 3°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = –30$ mA, $I_B = 0$	–60			V
Base-emitter saturation voltage	V_{BE}	$V_{CE} = –4$ V, $I_C = –3$ A			–1.8	V
Collector-emitter cutoff current ($V_{BE} = 0$)	I_{CES}	$V_{CE} = –60$ V, $V_{BE} = 0$			–200	µA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = –30$ V, $I_B = 0$			–300	µA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = –6$ V, $I_C = 0$			–1	mA
Forward current transfer ratio	h_{FE1}	$V_{CE} = –4$ V, $I_C = –1$ A	70		250	—
	h_{FE2}	$V_{CE} = –4$ V, $I_C = –3$ A	10			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = –3$ A, $I_B = –0.375$ A			–1.2	V
Transition frequency	f_T	$V_{CE} = –10$ V, $I_C = –0.5$ A, f = 10 MHz		30		MHz
Turn-on time	t_{on}	$I_C = –1$ A		0.5		µs
Storage time	t_{stg}	$I_{B1} = –0.1$ A, $I_{B2} = 0.1$ A		1.2		µs
Fall time	t_f	$V_{CC} = –50$ V		0.3		µs

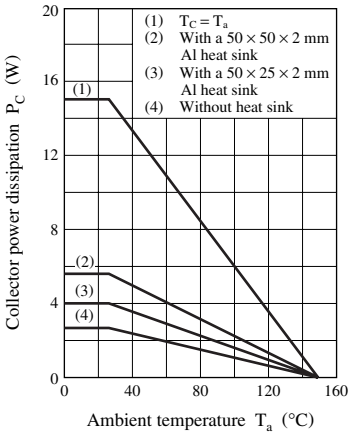
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Internal Connection

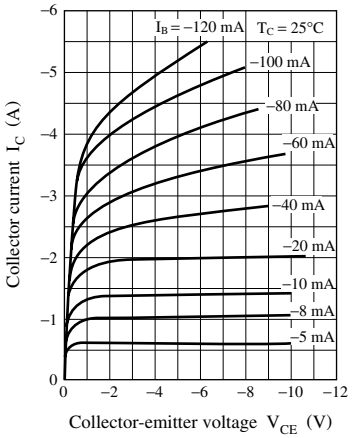


Note) The part number in the parenthesis shows conventional part number.

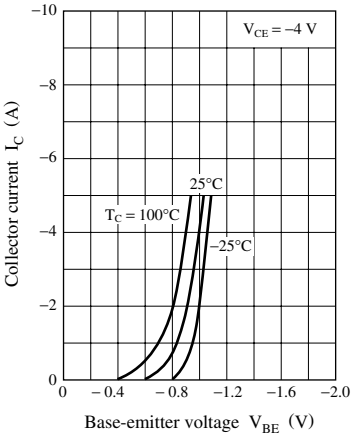
P_C — T_a



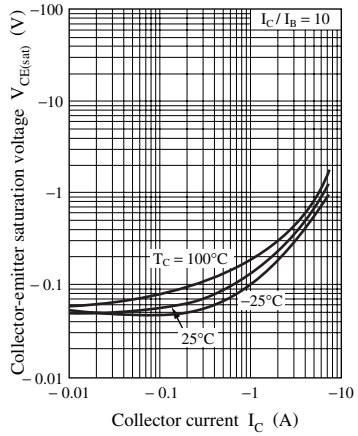
I_C — V_{CE}



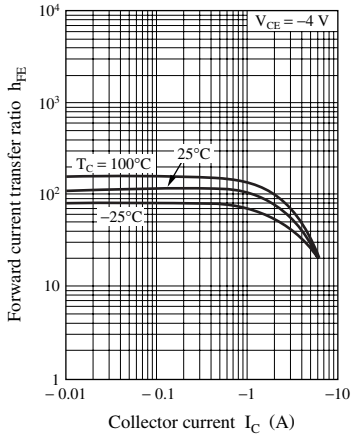
I_C — V_{BE}



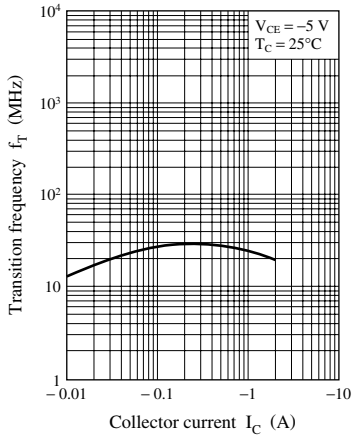
$V_{CE(sat)}$ — I_C



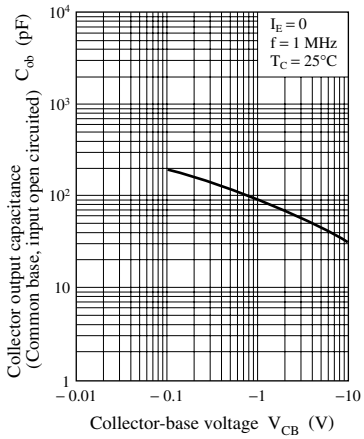
h_{FE} — I_C



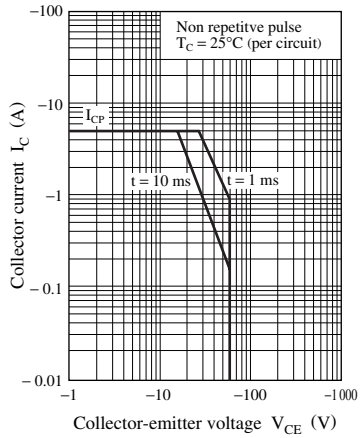
f_T — I_C



C_{ob} — V_{CB}



Safe operation area



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